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# PEMB15; PUMB15

PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

Rev. 5 — 16 December 2011

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			NPN/NPN	Package
	NXP	JEITA	complement	complement	configuration
PEMB15	SOT666	-	PEMD15	PEMH15	ultra small and flat lead
PUMB15	SOT363	SC-88	PUMD15	PUMH15	very small

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transisto	or					
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8.0	1	1.2	



# 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	[6] [5] [4]	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			1 2 3
			006aaa21

# 3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMB15	-	plastic surface-mounted package; 6 leads	SOT666	
PUMB15	SC-88	plastic surface-mounted package; 6 leads	SOT363	

# 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMB15	5D
PUMB15	B*6

[1] \* = placeholder for manufacturing site code

PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 4.7 kΩ

# 5. Limiting values

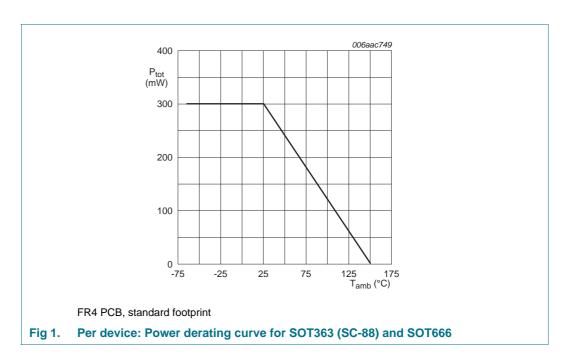
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V
$V_{EBO}$	emitter-base voltage	open collector	-	-10	V
$V_{I}$	input voltage				
	positive		-	+10	V
	negative		-	-30	V
Io	output current		-	-100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PEMB15 (SOT666)		[1][2]	200	mW
	PUMB15 (SOT363)		<u>[1]</u> _	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PEMB15 (SOT666)		[1][2] -	300	mW
	PUMB15 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



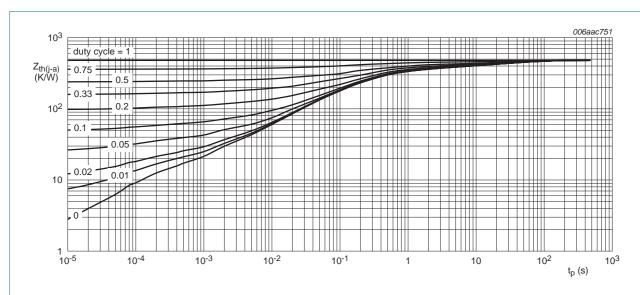
#### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMB15 (SOT666)		[1][2]	-	625	K/W
	PUMB15 (SOT363)		<u>[1]</u> _	-	625	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMB15 (SOT666)		[1][2] _	-	417	K/W
	PUMB15 (SOT363)		<u>[1]</u> -	-	417	K/W

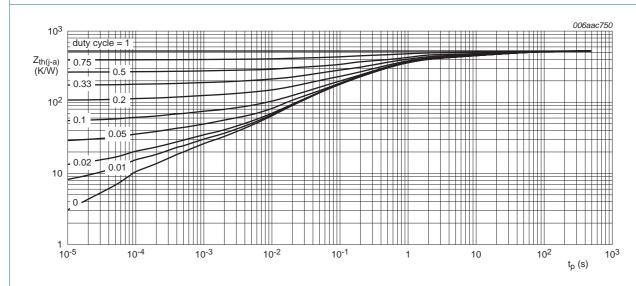
<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMB15 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMB15 (SOT363); typical values

PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 4.7 kΩ

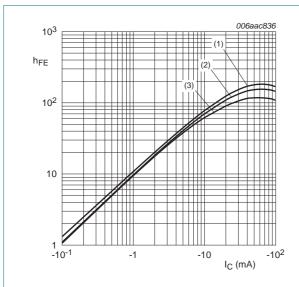
## 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

ramb — 20	o unicos otrici vioc spec	moa.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	-1	μΑ
	current	$V_{CE} = -30 \text{ V; } I_{B} = 0 \text{ A;}$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	<b>-5</b>	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-900	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-1.1	-0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V};$ $I_{C} = -20 \text{ mA}$	-2.5	-1.9	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	$k\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -10 \text{ mA;}$ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor



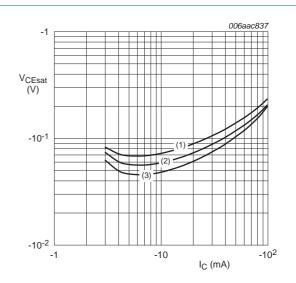
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 4. DC current gain as a function of collector current; typical values



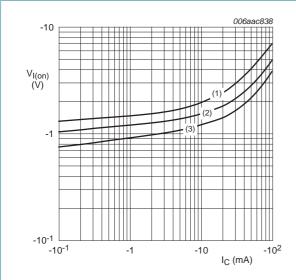
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



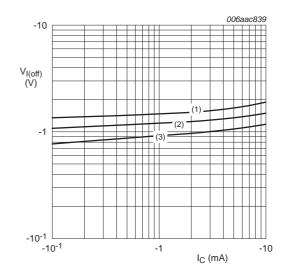
$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 6. On-state input voltage as a function of collector current; typical values



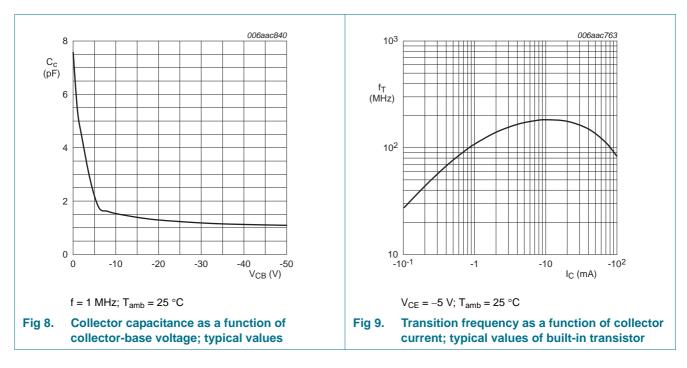
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 7. Off-state input voltage as a function of collector current; typical values

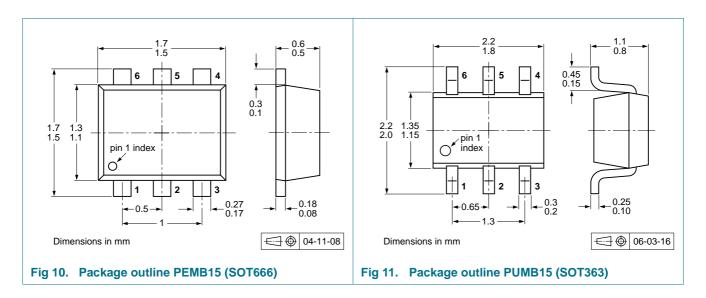


#### 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 9. Package outline



PEMB15\_PUMB15

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# 10. Packing information

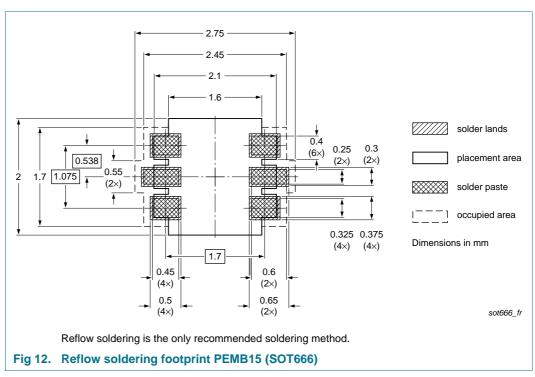
Table 9. Packing methods

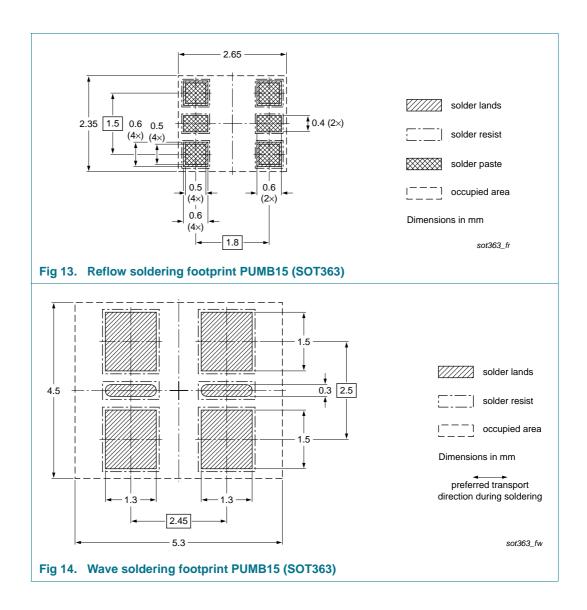
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре	Package	e Description		Packing quantity				
number			3000	4000	8000	10000		
PEMB15	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-		
		4 mm pitch, 8 mm tape and reel	-	-115	-	-		
PUMB15	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135		
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165		

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

# 11. Soldering





PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 4.7 kΩ

# 12. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB15_PUMB15 v.5	20111216	Product data sheet	-	PEMB15_PUMB15 v.4
Modifications:	<ul> <li>Section 4 "N</li> <li>Figure 1 to 3</li> <li>Section 6 "T</li> <li>Figure 4 to 9</li> <li>Table 8 "Ch</li> <li>Section 8 "T</li> <li>Section 9 "F</li> <li>Section 11 "</li> </ul>	hermal characteristics": up	f <sub>T</sub> added ed by minimized packag	e outline drawings
PEMB15_PUMB15 v.4	20090831	Product data sheet	-	PEMB15_PUMB15 v.3
PEMB15_PUMB15 v.3	20050203	Product data sheet	-	PUMB15 v.2
PUMB15 v.2	20040414	Product specification	-	PUMB15 v.1
PUMB15 v.1	20031107	Product specification	-	-

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMB15\_PUMB15

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# PEMB15; PUMB15

PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

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